

C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

47. (amended) An integrated circuit comprising:

a semiconductive substrate;

a layer comprising a first metal over the substrate;

a layer of alloy material within the layer comprising the first metal, the alloy material layer comprising the first metal and a second metal different from the first metal, the second metal comprising palladium, magnesium, or both; and

a conductive connection on the alloy layer.

48. (amended) The integrated circuit of claim 47 wherein the alloy material consists of an intermetallic.

52. (amended) The integrated circuit of claim 47 wherein the second metal comprises palladium.

55. (new) An integrated circuit comprising:
a semiconductive substrate;
a layer comprising Cu over the substrate;
a layer of alloy material within the layer comprising Cu, the alloy material layer comprising intermetallic Cu_3Ti ; and
a conductive connection on the alloy layer.
56. (new) The integrated circuit of claim 55 wherein the alloy material consists essentially of Cu_3Ti .
57. (new) The integrated circuit of claim 55 wherein about 50 to about 300 Angstroms of the first metal layer is alloy material.
58. (new) The integrated circuit of claim 55 wherein the conductive connection comprises an integrated circuit via or an integrated circuit wire bond.
59. (new) An integrated circuit comprising:
a semiconductive substrate;
a layer consisting of copper over the substrate;
a layer of alloy material within the copper layer, the alloy material layer consisting of copper and a second metal, the second metal consisting of palladium, magnesium, or both; and
a conductive connection on the alloy layer.